

RF Power MOSFET Transistor 15 W, 2 - 175 MHz, 12 V

Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than bipolar devices
- Specifically designed for 12 volt applications
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I _{DS}	4	А
Power Dissipation	PD	87.5	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	2	°C/W

TYPICAL DEVICE IMPEDANCE

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)			
30	3.0 - j25	4.0 - j3.0			
100	3.0 - j15	3.5 - j1.5			
175	5.0 - j8	4.0 - j0.0			
V _{DD} = 12V, I _{DQ} = 100mA, P _{OUT} = 15W					

 $Z_{\mbox{\scriptsize IN}}$ is the series equivalent input impedance of the device from gate to source.

 $Z_{\mbox{\scriptsize LOAD}}$ is the optimum series equivalent load impedance as measured from drain to ground.

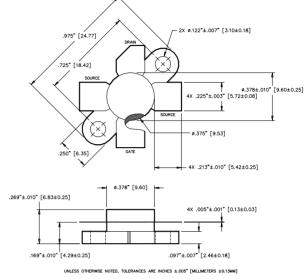
ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	40	-	V	$V_{GS} = 0.0 \text{ V}$, $I_{DS} = 5.0 \text{ mA}$
Drain-Source Leakage Current	I _{DSS}	-	1.0	mA	V_{GS} = 15.0 V , V_{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	1.0	μA	V_{GS} = 20.0 V , V_{DS} = 0.0 V
Gate Threshold Voltage	V _{GS(TH)}	20	6.0	V	V _{DS} = 10.0 V , I _{DS} = 100 mA
Forward Transconductance	G _M	0.5	-	S	V_{DS} = 10.0 V , I_{DS} = 1000 mA , Δ V_{GS} = 1.0 V
Input Capacitance	CISS	-	50	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Output Capacitance	C _{OSS}	-	60	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	12	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Power Gain	G _P	9.5	-	dB	V_{DD} = 12.0 V, I_{DQ} = 100 mA, P_{OUT} = 15 W F =175 MHz
Drain Efficiency	ŋ₀	60	-	%	V_{DD} = 12.0 V, I_{DQ} = 100 mA, P_{OUT} = 15 W F =175 MHz
Load Mismatch	VSWR-T	-	30:1	-	V_{DD} = 12.0 V, I_{DQ} = 100 mA, P_{OUT} = 15 W F =175 MHz

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Package Outline



LETTER	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
А	24.64	24.89	.970	.980	
В	18.29	18.54	.720	.730	
С	20.07	20.83	.790	.820	
D	9.47	9.73	.373	.383	
E	6.22	6.48	.245	.255	
F	5.64	5.79	.222	.228	
G	2.92	3.30	.115	.130	
н	2.29	2.67	.090	.105	
J	4.04	4.55	.159	.179	
К	6.58	7.39	.259	.291	
L	.10	.15	.004	.006	

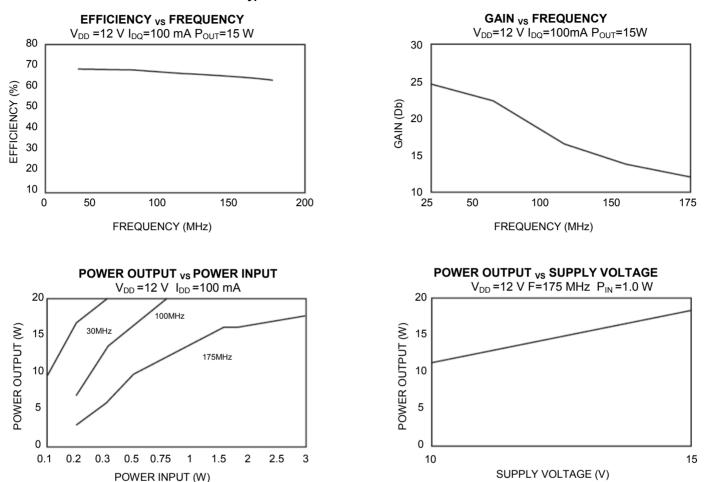
Rev. V1





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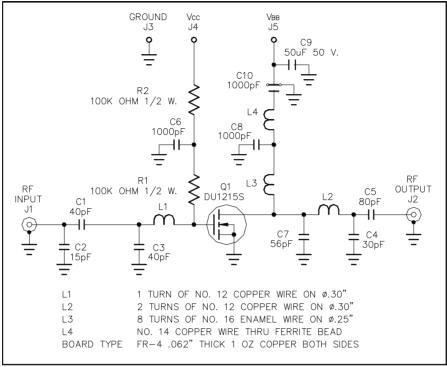
Typical Broadband Performance Curves

2

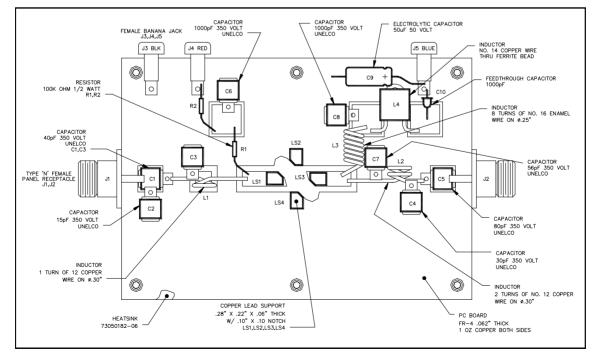
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TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY





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Rev. V1

DU1215S

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Rev. V1

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